

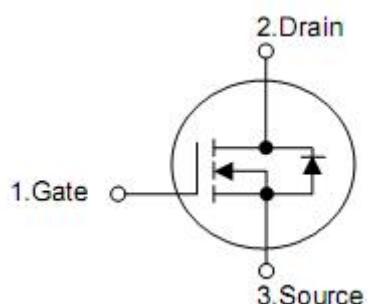
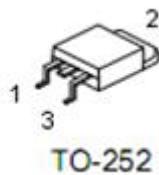
1. Features

- $R_{DS(on)}=4.5\text{m}\Omega$ @ $V_{GS}=10\text{V}$
- Lead free and Green Device Available
- Low Rds-on to Minimize Conductive Loss
- High avalanche Current

2. Application

- Load Switch
- SMPS

3. Pin configuration



Pin	Function
1	Gate
2	Drain
3	Source

4. Ordering Information

Part Number	Package	Brand
KND3403A	TO-252	KIA

5. Absolute maximum ratings

TC=25 °C unless otherwise specified

Parameter	Symbol	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}	30	V
Gate-to-Source Voltage	V _{GSS}	±20	
Continuous Drain Current	T _C =25 °C(Silicon limited)	85	A
	T _C =100 °C(Silicon limited)	61	
	T _C =25 °C(Package limited)	50	
	T _C =25 °C(Silicon limited)	76	
	T _C =100 °C(Silicon limited)	54	
	T _C =25 °C(Package limited)	50	
Pulsed Drain Current Tested	I _{DM}	340	
Avalanche Current (L=0.5mH)	I _{AS}	25	A
Avalanche Energy (L=0.5mH)	E _{AS}	156	mJ
Maximum power Dissipation	T _C =25 °C	71	W
	T _C =100 °C	35	
Junction & Storage Temperature Range	T _J & T _{STG}	-55 to 175	°C

6. Thermal characteristics

Parameter	Symbol	Ratings	Units
Thermal resistance, Junction-case	R _{θJC}	2.1	°C/W
Thermal resistance, junction-ambient	R _{θJA}	106	°C/W

7. Electrical characteristics

($T_J=25^\circ\text{C}$, unless otherwise notes)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_D=250\mu\text{A}$	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$\text{V}_{\text{DS}}=24\text{V}, \text{V}_{\text{GS}}=0\text{V}$	-	-	1	μA
Gate threshold voltage	$\text{V}_{\text{GS}(\text{th})}$	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_D=250\mu\text{A}$	0.8	-	2.0	V
Gate leakage current	I_{GSS}	$\text{V}_{\text{GS}}=\pm 20\text{V}, \text{V}_{\text{DS}}=0\text{V}$	-	-	± 100	nA
Drain-source on-resistance	$\text{R}_{\text{DS}(\text{on})}$	$\text{V}_{\text{GS}}=10\text{V}, \text{I}_D=30\text{A}$	-	4.5	5.5	$\text{m}\Omega$
		$\text{V}_{\text{GS}}=4.5\text{V}, \text{I}_D=30\text{A}$	-	5.5	7	
Forward Transconductance	g_{fs}	$\text{V}_{\text{DS}}=5\text{V}, \text{I}_D=90\text{A}$	-	74	-	S
Dynamic characteristics						
Gate Resistance	R_G	$\text{V}_{\text{GS}}=0\text{V}, \text{V}_{\text{DS}}=0\text{V}$ Frequency=1MHz	-	2.0	-	Ω
Input capacitance	C_{iss}	$\text{V}_{\text{DS}}=15\text{V}, \text{V}_{\text{GS}}=0\text{V},$ $F=1\text{MHz}$	-	3000	-	pF
Output capacitance	C_{oss}		-	330	-	pF
Reverse transfer capacitance	C_{rss}		-	285	-	pF
Turn-on delay time	$t_{\text{d}(\text{on})}$	$\text{V}_{\text{DS}}=15\text{V}, \text{I}_D=1\text{A},$ $\text{V}_{\text{GS}}=4.5\text{V}, \text{R}_G=3\Omega$	-	20	-	ns
Rise time	t_r		-	32	-	ns
Turn-off delay time	$t_{\text{d}(\text{off})}$		-	60	-	ns
Fall time	t_f		-	33	-	ns
Gate Charge Characteristics						
Total gate charge	Q_g	$\text{V}_{\text{DS}}=25\text{V}, \text{I}_D=14\text{A},$ $\text{V}_{\text{GS}}=4.5\text{V}$	-	25	-	nC
Gate-source charge	Q_{gs}		-	3.2	-	nC
Gate-drain charge	Q_{gd}		-	12	-	nC
Diode characteristics						
Diode forward voltage	V_{SD}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_{\text{SD}}=25\text{A}$	-	0.82	1.3	V
Drain Continuous Forward current	I_S		-	-	50	A
Reverse recovery time	t_{rr}	$I_S=20\text{A}$ $\text{di}/\text{dt}=100\text{A}/\mu\text{s}$	-	14	-	ns
Reverse recovery charge	Q_{rr}		-	2.8	-	μC

8. Typical Characteristics

Figure 1. Typ. Output Characteristics

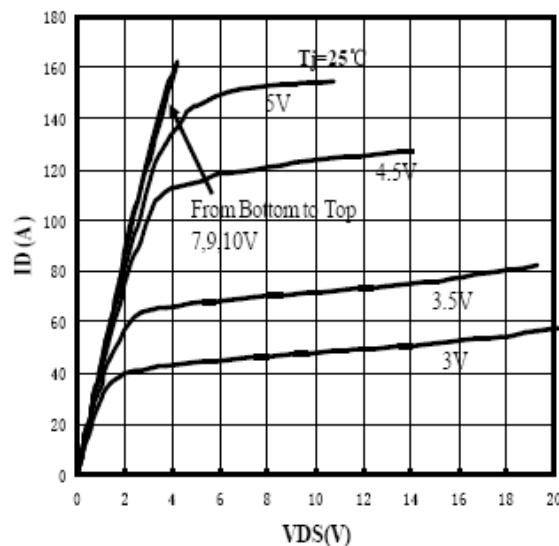


Figure 2. Typ. Output Characteristics

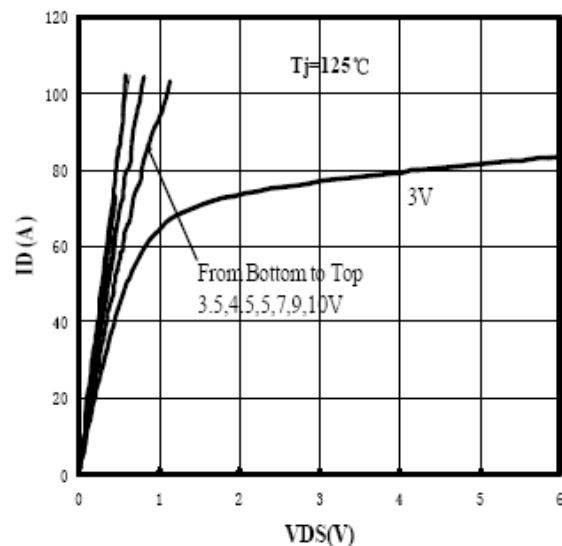


Figure 3. Transfer Characteristics

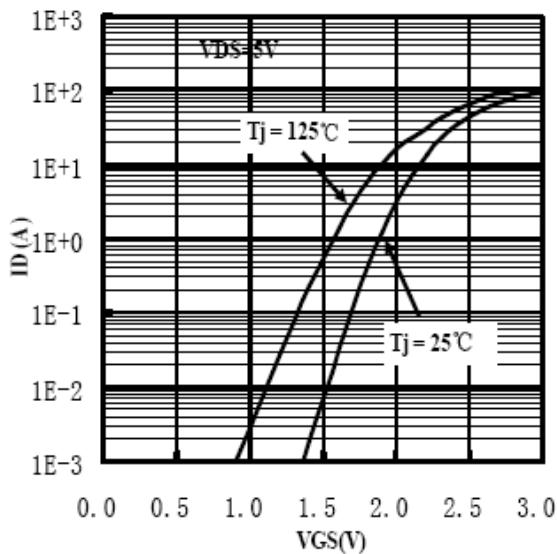


Figure 4. Gate Threshold Voltage Characteristics

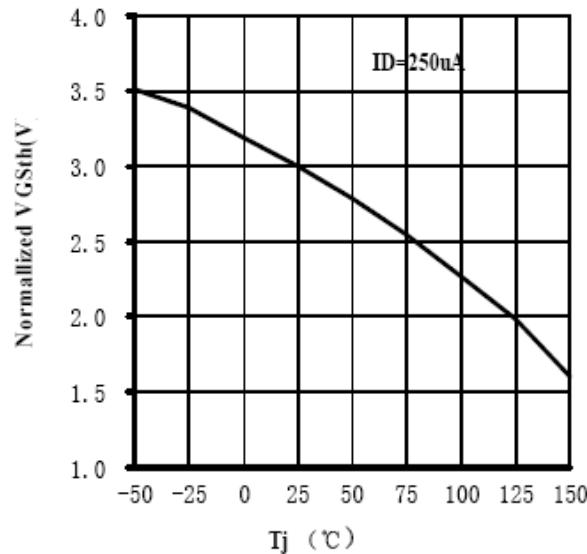


Figure 5. Rdson vs. Drain Current Characteristics

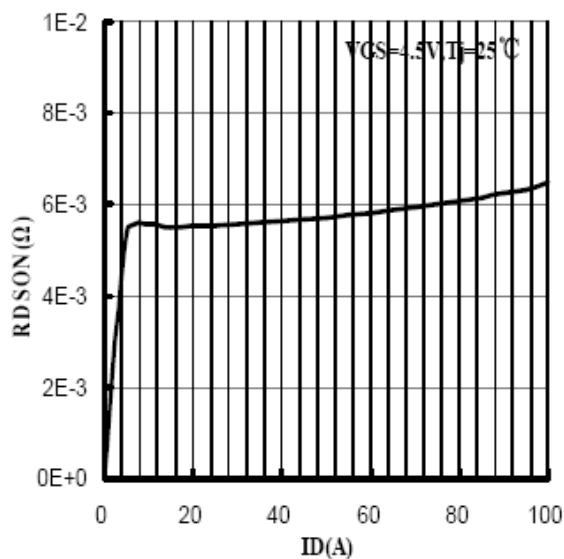


Figure 7. Rdson vs. VGS Characteristics

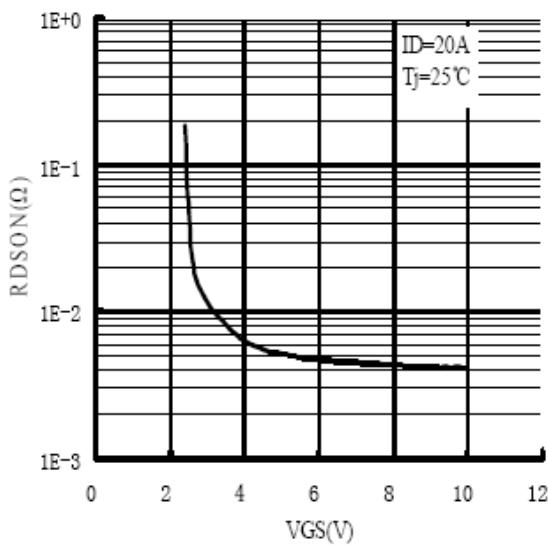


Figure 6. Rdson vs. Junction Temp Characteristics

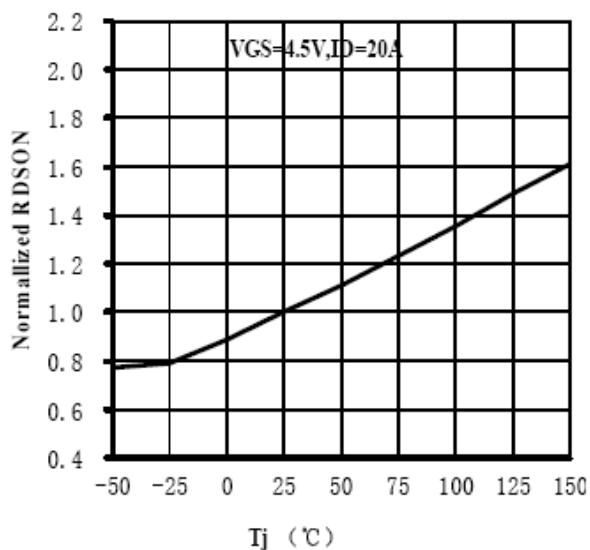


Figure 8. IS vs. VSD Characteristics

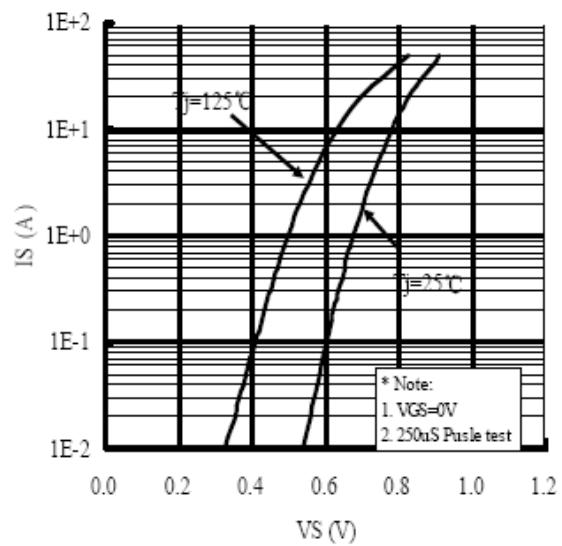


Figure 9. Gate Charge Characteristics

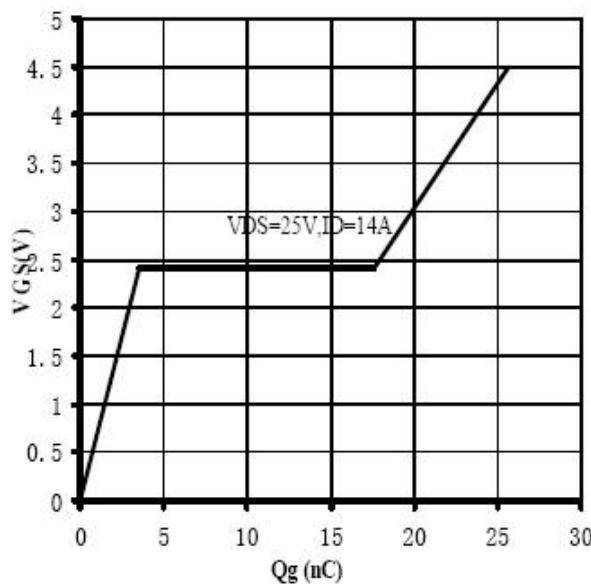


Figure 10. Capacitance Characteristics

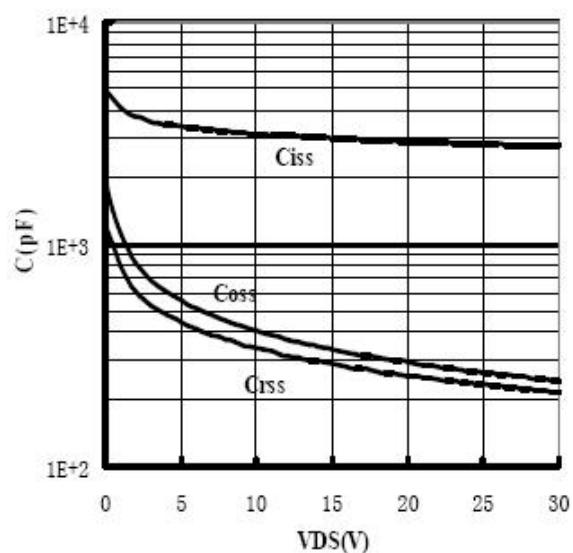
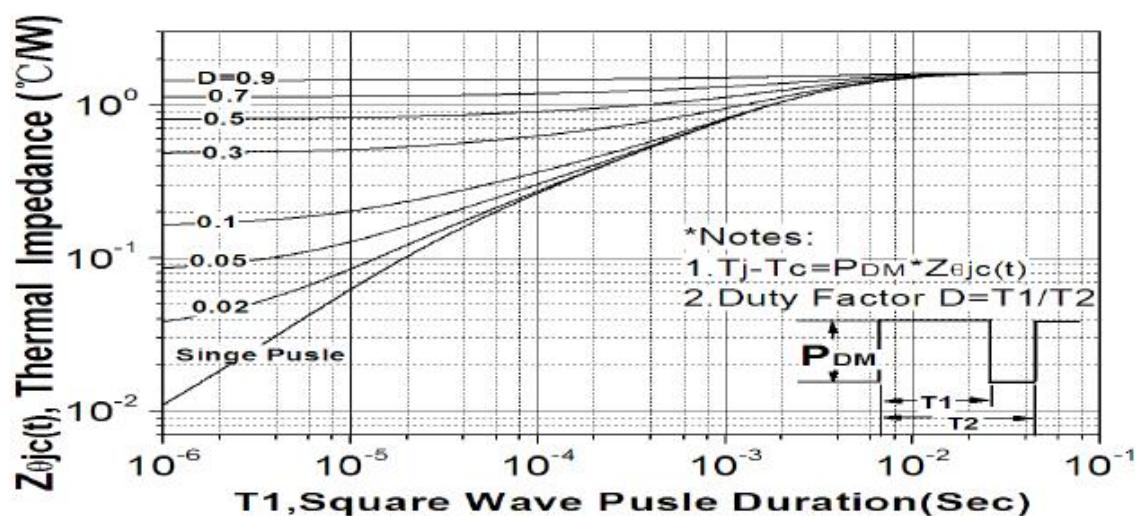
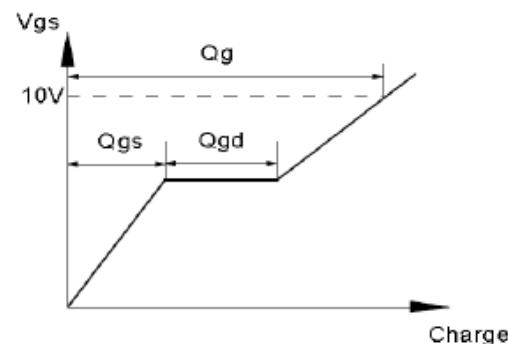
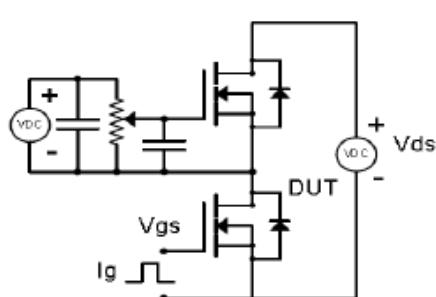


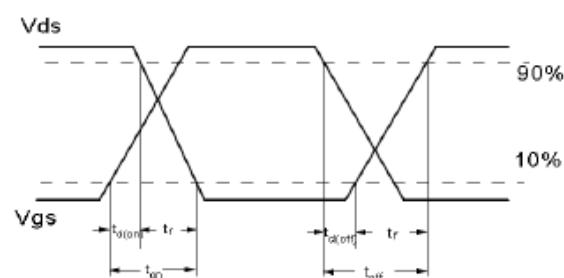
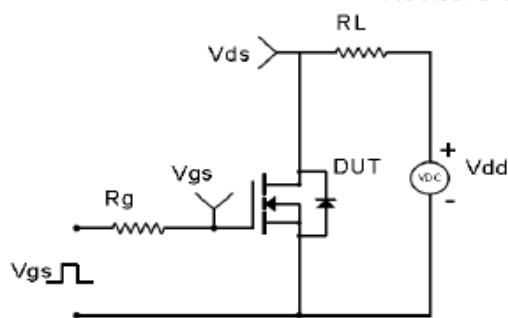
Figure 11. Thermal Resistance Characteristics



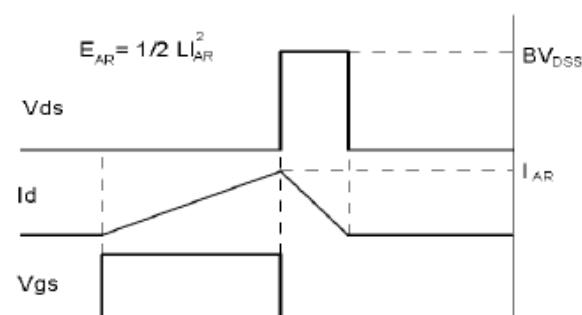
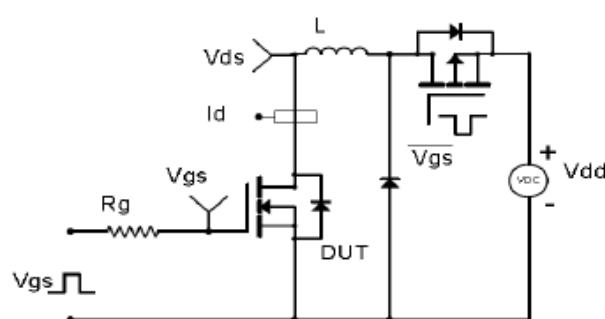
Gate Charge Test Circuit & Waveform



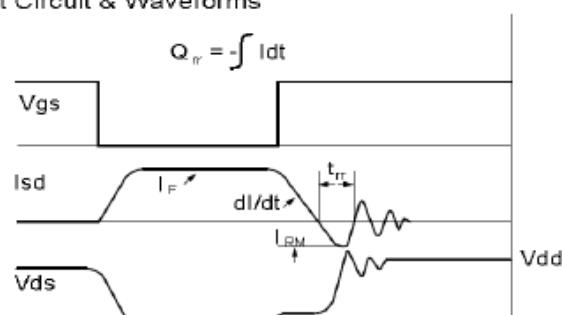
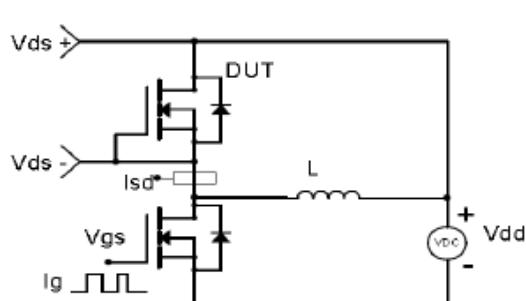
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



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